

SILICON POWER TRANSISTOR 2SC4553

NPN SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SC4553 is a power transistor designed especially for low collector saturation voltage and features large current switching at a low power dissipation. In addition, a high hee enables alleviation of the driver load.

FEATURES

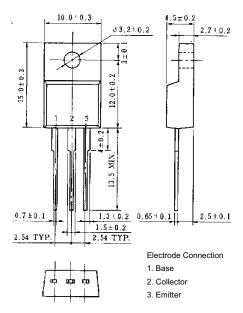
- High hre and low VcE(sat): hre $\cong 800$ (VcE = 2 V, Ic = 3 A) $VcE(sat) \cong 0.12$ V (Ic = 3 A, IB = 0.03 A)
- On-chip C to E damper diode
- Mold package that does not require an insulating board or insulation bushing

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V _{СВО}	100	٧
Collector to emitter voltage	VCEO	100	V
Emitter to base voltage	V _{EBO}	7.0	٧
Collector current (DC)	Ic(DC)	±7.5	Α
Collector current (pulse)	IC(pulse)*	±10	Α
Base current (DC)	I _{B(DC)}	2.0	Α
Total power dissipation	P⊤ (Tc = 25°C)	30	W
Total power dissipation	P⊤ (Ta = 25°C)	2.0	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

^{*} PW \leq 10 ms, duty cycle \leq 50%

PACKAGE DRAWING (UNIT: mm)



EQUIVALENT CIRCUIT



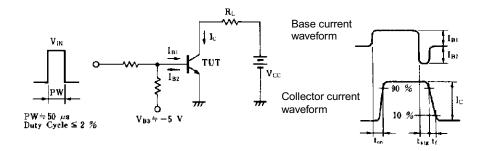
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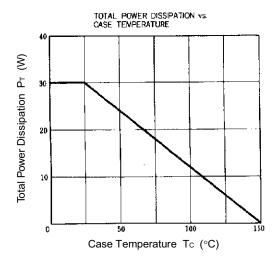
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

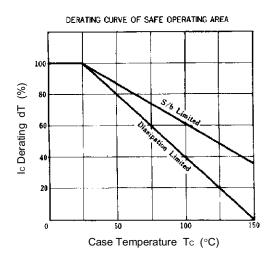
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	V _{CB} = 100 V, I _E = 0			10	μΑ
Emitter cutoff current	ІЕВО	V _{EB} = 5.0 V, I _C = 0			17	mA
DC current gain	h _{FE1}	Vce = 2.0 V, Ic = 3.0 A	450	800	2,000	
DC current gain	h _{FE2}	Vce = 2.0 V, Ic = 5.0 A	150			
Collector saturation voltage	VCE(sat)1	Ic = 3.0 A, I _B = 60 mA			0.2	V
Collector saturation voltage	VCE(sat)2	Ic = 3.0 A, I _B = 30 mA		0.12	0.3	V
Collector saturation voltage	VCE(sat)3	Ic = 5.0 A, I _B = 100 mA			0.4	V
Collector saturation voltage	VCE(sat)4	Ic = 5.0 A, Iв = 50 mA			0.55	V
Base saturation voltage	V _{BE(sat)}	Ic = 5.0 A, Iв = 50 mA			1.2	V
Gain bandwidth product	f⊤	Vce = 5.0 V, Ic = 0.5 A		100		MHz
Collector capacitance	Cob	VcB = 10 V, IE = 0, f = 1 MHz		110		pF
Turn-on time	ton	Ic = 5.0 A, R _L = 3.0 Ω , I _{B1} = -I _{B2} = 100 mA, V _{CC} \cong 16 V Refer to the test circuit.		0.5		μs
Storage time	t stg			2.0		μs
Fall time	tf			0.5		μs
Diode forward voltage	V _{DF}	I _{DF} = 5.0 A		1.4		V

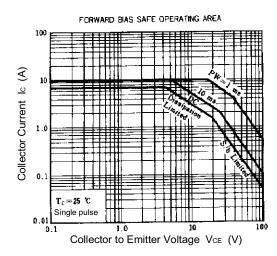
SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT

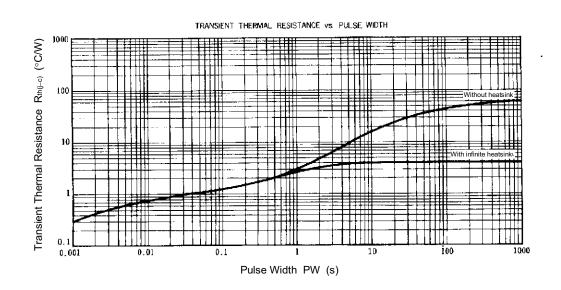


TYPICAL CHARACTERISTICS (Ta = 25°C)

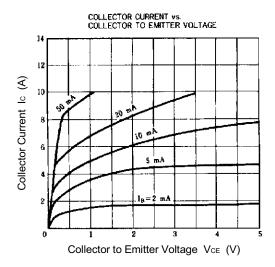


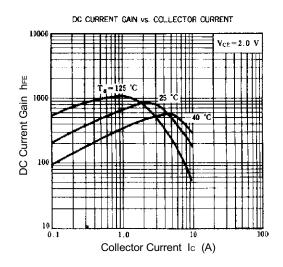


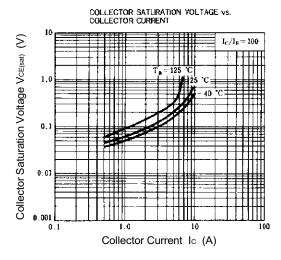


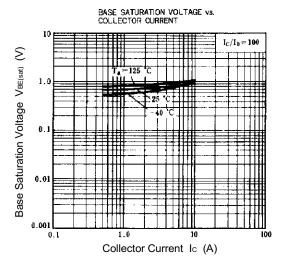


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